

# MICRO

查询2N4029供应商

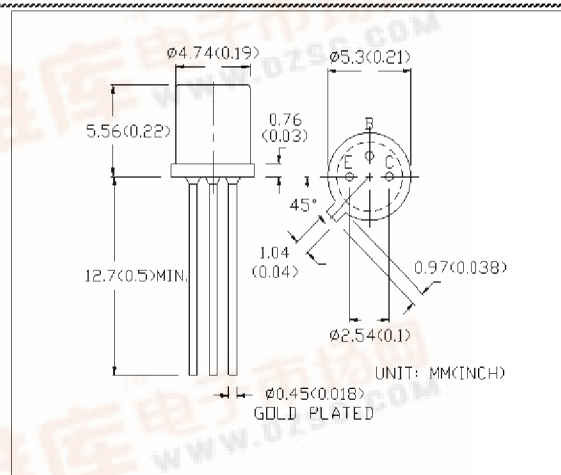
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2N4029

PNP  
SILICON  
TRANSISTOR

## DESCRIPTION

2N4029 is PNP silicon planar epitaxial transistor for AF medium power drivers and outputs.



## ABSOLUTE MAXIMUM RATINGS

|                                          |          |               |
|------------------------------------------|----------|---------------|
| Collector-Base Voltage                   | VCBO     | 80V           |
| Collector-Emitter Voltage                | VCEO     | 80V           |
| Emitter-Base Voltage                     | VEBO     | 5V            |
| Collector Current                        | IC       | 1A            |
| Continuous Power Dissipation             | Pd       | 800mW         |
| Operating & Storage Junction Temperature | Tj, Tstg | -65 to +150°C |

## ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25°C)

| PARAMETER                            | SYMBOL    | MIN | MAX  | UNIT | CONDITIONS            |
|--------------------------------------|-----------|-----|------|------|-----------------------|
| Collector-Base Breakdown Voltage     | BVCBO     | 80  |      | V    | IC = 10μA IE = 0      |
| Collector-Emitter Breakdown Voltage  | LVCEO*    | 80  |      | V    | IC = 10mA IB = 0      |
| Emitter-Base Breakdown Voltage       | BVEBO     | 5   |      | V    | IE = 10μA IC = 0      |
| Collector Cutoff Current             | ICBO      |     | 50   | nA   | VCB = 60V IE = 0      |
| D.C. Current Gain                    | HFE*      | 75  |      |      | IC = 0.1mA VCE = 5V   |
|                                      |           | 100 | 300  |      | IC = 100mA VCE = 5V   |
|                                      |           | 70  |      |      | IC = 500mA VCE = 5V   |
|                                      |           | 25  |      |      | IC = 1A VCE = 5V      |
| Collector-Emitter Saturation Voltage | VCE(sat)* |     | 0.15 | V    | IC = 150mA IB = 15mA  |
|                                      |           |     | 0.5  | V    | IC = 500mA IB = 50mA  |
| Base-Emitter Saturation Voltage      | VBE(sat)* |     | 0.9  | V    | IC = 150mA IB = 15mA  |
| Base-Emitter Voltage                 | VBE*      |     | 1.1  | V    | IC = 500mA VCE = 0.5V |
| Current Gain Bandwidth Product       | fT        | 150 |      | MHz  | IC = 50mA VCE = 10V   |
| Output Capacitance                   | Cob       |     | 20   | pF   | VCB = 10V f = 1MHz    |
| Input Capacitance                    | Cib       |     | 110  | pF   | VEB = 0.5V f = 1MHz   |

\*Pulse Test : pulse width < 300μS, duty cycle < 2%.

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